

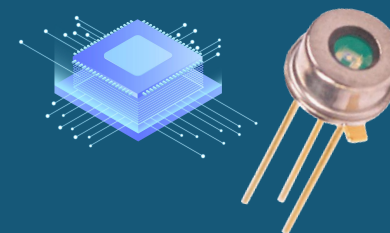
InGaAs Photodetector 2000 μ m (TO-CAN)

Features

- Bright Surface 2000 μ m
- To-5 Package
- Long Wavelength Operation
- Low Dark Current
- High Responsivity

Application

- Monitoring and Meter
- Optical Instruments
- Power Monitoring
- Test equipment



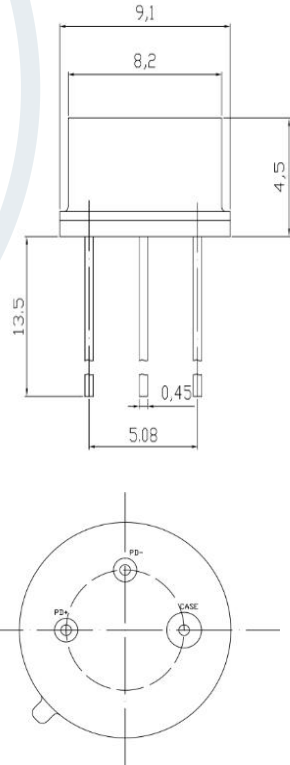
Absolute Maximum Ratings (Tc=25°C .unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit	Test Condition
Forward Current	I_{FP}	–	10	mA	CW
Reverse Current	I_R	–	10	mA	CW
Operating Temperature	T_{OP}	–20	+70	°C	–
Storage Temperature	T_{stg}	–40	+100	°C	–
Soldering Temperature/Time	–	260/10		°C/S	–

Specifications (electrical & optical characteristics) T= 25 ℃

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Wavelength Range	λ	800	–	1700	nm	–
Active Area	Φ	–	2000	–	$\mu\text{ m}$	–
Saturated Optical Power	P _s	10	–	–	dBm	V _R = 0V
Dark Current	I _d	–	–	8	nA	V _R = 5V
Responsibility	Res	0.85 @ 1310nm			A / W	ϕ e=100 μ w, λ =1310nm
		0.90 @ 1550nm				ϕ e=100 μ w, λ =1550nm
Capacitance	C _t	–	–	250	pF@ Φ 2000	V _R =5V, f = 1 MHz
Reverse Breaksown V	V _{BR}	35	–	–	v	I _d =10 μ A, ϕ e=0
Input Power Range	P	–70	–	6	dBm	V _R =5V, R _L = 50 Ω
		–60	–	16		
		–50	–	26		
		–40	–	36		

Pin Assignment



Order Information

GTA2006	(InGaAs Photo-detector	2000 μ m)
GTA2007	(InGaAs Photo-detector	1000 μ m)
GTA2008	(InGaAs Photo-detector	300 μ m)
GTA2009	(InGaAs Photo-detector	5000 μ m)
GTA2010	(InGaAs Photo-detector	10000 μ m)



Please let us know your request details before order.



Customize for you

